

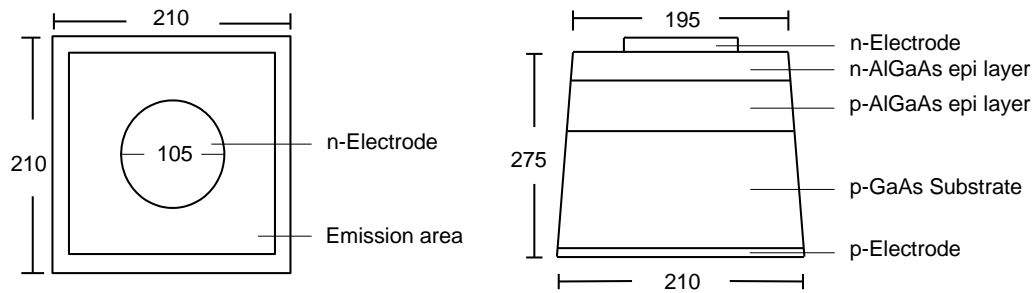
### ■ Features :

- AlGaAs/GaAs Epi Wafer
- Double Hetero-junction Structure
- High Brightness

### ■ Typical Applications :

- Lamp
- Display

### ■ Outline Dimensions : (Unit: $\mu\text{m}$ )



### ■ Physical Structure :

Chip dimension	Chip size	210 $\mu\text{m}$ x 210 $\mu\text{m}$
	Thickness	275 $\mu\text{m}$
	Emission area	195 $\mu\text{m}$
	Bonding pad	105 $\mu\text{m}$
Electrode	Top: N (cathode)	Aluminum (Gold optional)
	Backside: P (anode)	Gold alloy
Surface condition	Not frosted	

### ■ Electro-Optical Characteristics : ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 20 \text{ mA}$	-	1.88	2.10	V
Reverse Current	$I_R$	$V_R = 5 \text{ V}$	-	-	10	$\mu\text{A}$
*1 Wavelength	$\lambda_P$	$I_F = 20 \text{ mA}$	-	655	-	nm
	Hue		-	644	-	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Reverse Voltage	$V_R$	$I_R = 10 \text{ uA}$	5.0	-	-	V
*1 Luminous Intensity	$I_V$	$I_F = 20 \text{ mA}$	15.0	-	-	mcd

\*1 Data on label shows OPTO TECH readings which are measured by sampling 40 pieces per wafer.

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

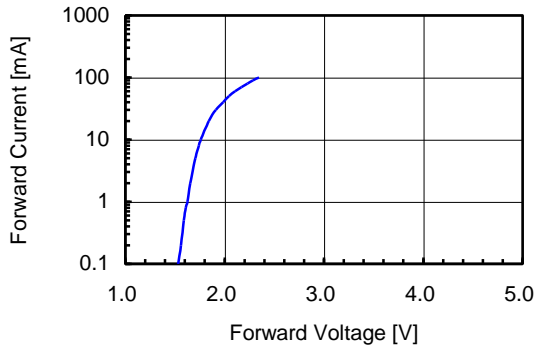


Fig 2. Relative Intensity vs. Forward Current

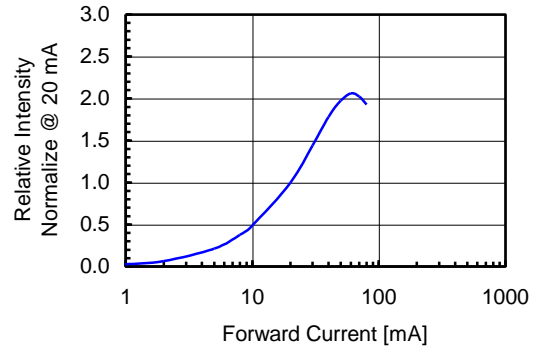


Fig 3. Forward Voltage vs. Temperature

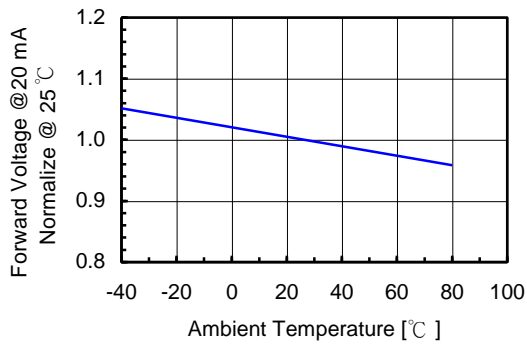


Fig 4. Relative Intensity vs. Temperature

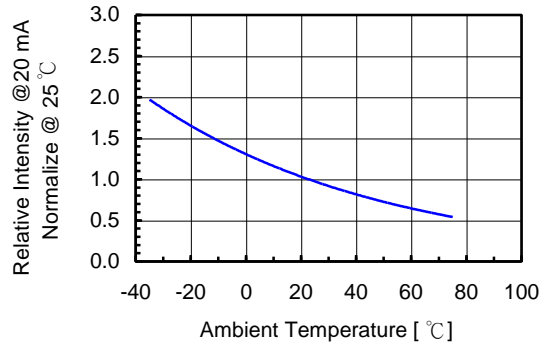


Fig 5. Relative Intensity vs. Wavelength

